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# ***Nanoepitaxy: Materials and Devices V***

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**25–27 August 2013**  
**San Diego, California, United States**

*Sponsored and Published by*  
SPIE

**Volume 8820**

Proceedings of SPIE 0277-786X, V. 8820

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Nanoepitaxy: Materials and Devices V, edited by Nobuhiko P. Kobayashi, A. Alec Talin,  
Albert V. Davydov, M. Saif Islam, Proc. of SPIE Vol. 8820, 882001 · © 2013 SPIE  
CCC code: 0277-786X/13/\$18 · doi: 10.1117/12.2033974

Proc. of SPIE Vol. 8820 882001-1

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Author(s), "Title of Paper," in *Nanoepitaxy: Materials and Devices V*, edited by Nobuhiko P. Kobayashi, A. Alec Talin, Albert V. Davydov, M. Saif Islam, Proceedings of SPIE Vol. 8820 (SPIE, Bellingham, WA, 2013) Article CID Number.

ISSN: 0277-786X

ISBN: 9780819496706

Published by

**SPIE**

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445

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